TN0620

N-Channel Enhancement-Mode Vertical DMOS FET

Features

- · 1.6V Maximum Low Threshold
- · High Input Impedance
- · 110 pF Typical Low Input Capacitance
- · Fast Switching Speeds
- · Low On-Resistance
- · Free from Secondary Breakdown
- · Low Input and Output Leakage

Applications

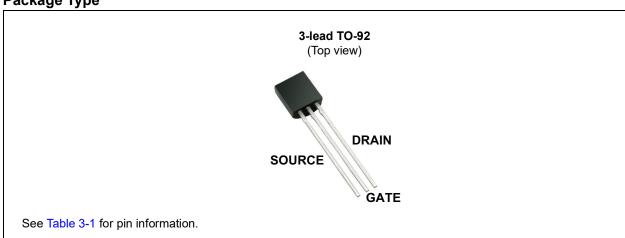
- Logic-Level Interfaces (Ideal for TTL and CMOS)
- · Solid-State Relays
- · Battery-Operated Systems
- · Photovoltaic Drives
- · Analog Switches
- General Purpose Line Drivers
- · Telecommunication Switches

General Description

The TN0620 low-threshold, Enhancement-mode (normally-off) transistor uses a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Type



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

Drain-to-Source Voltage	BV _{DSS}
Drain-to-Gate Voltage	500
Gate-to-Source Voltage	
Operating Ambient Temperature, T _A	
Storage Temperature, T _S	

† Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Electrical Specifications: $T_A = 25^{\circ}$ C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. (Pulse test: 300 µs pulse, 2% duty cycle)

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions
Drain-to-Source Breakdown Voltage	BV _{DSS}	200		_	V	$V_{GS} = 0V$, $I_D = 2 \text{ mA}$
Gate Threshold Voltage	V _{GS(th)}	0.6	_	1.6	V	$V_{GS} = V_{DS}$, $I_D = 1 \text{ mA}$
Change in V _{GS(th)} with Temperature	$\Delta V_{GS(th)}$	_	_	-5	mV/°C	V _{GS} = V _{DS} , I _D = 1 mA (Note 1)
Gate Body Leakage Current	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
		_		10	μA	V _{GS} = 0V, V _{DS} = Maximum rating
Zero-Gate Voltage Drain Current	I _{DSS}	_		1	mA	V_{DS} = 0.8 Maximum rating, V_{GS} = 0V, T_A = 125°C (Note 1)
On-State Drain Current	l	0.5		_	Α	$V_{GS} = 5V, V_{DS} = 25V$
On-State Drain Guirent	I _D (ON)	1		_	Α	$V_{GS} = 10V, V_{DS} = 25V$
Static Drain-to-Source On-State Resistance	В	_	6	8	Ω	$V_{GS} = 5V, I_D = 250 \text{ mA}$
Static Dialif-to-Source Off-State Resistance	R _{DS(ON)}	_	4	6	Ω	V_{GS} = 10V, I_{D} = 500 mA
Change in R _{DS(ON)} with Temperature	ΔR _{DS(ON)}	_	_	1.4	%/°C	V _{GS} = 10V, I _D = 500 mA (Note 1)

Note 1: Specification is obtained by characterization and is not 100% tested.

AC ELECTRICAL CHARACTERISTICS

Electrical Specifications: T_A = 25°C unless otherwise specified. All AC parameters are sample tested. Specification is obtained by characterization and is not 100% tested.

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions	
Forward Transconductance	G _{FS}	300	400	_	mmho	V _{DS} = 25V, I _D = 500 mA	
Input Capacitance	C _{ISS}	_	110	150	pF	$V_{GS} = 0V$,	
Common-Source Output Capacitance	Coss	_	40	85	pF	V _{DS} = 25V,	
Reverse Transfer Capacitance	C _{RSS}	_	10	35	pF	f = 1 MHz	
Turn-On Delay Time	t _{d(ON)}	_	_	10	ns		
Rise Time	t _r	_	_	8	ns	V _{DD} = 25V,	
Turn-Off Delay Time		_	_	20	ns	I _D = 1A, R _{GEN} = 25Ω	
Fall Time	t _f	_	_	20	ns	GEN	
DIODE PARAMETER							
Diode Forward Voltage Drop	V_{SD}	_	_	1.8	V	V _{GS} = 0V, I _{SD} = 1A (Note 1)	
Reverse Recovery Time	t _{rr}		300	_	ns	V _{GS} = 0V, I _{SD} = 1A	

Note 1: All DC parameters are 100% tested at 25°C unless otherwise stated. (Pulse test: 300 µs pulse, 2% duty cycle)

TEMPERATURE SPECIFICATIONS

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions	
TEMPERATURE RANGE							
Operating Ambient Temperature	T _A	-55	_	+150	°C		
Storage Temperature	T _S	-55	_	+150	°C		
PACKAGE THERMAL RESISTANCE							
3-lead TO-92	θ_{JA}	_	132	_	°C/W		

THERMAL CHARACTERISTICS

Package	I _D (Note 1) (Continuous) (mA)	I _D (Pulsed) (A)	Power Dissipation at T _A = 25°C (W)	I _{DR} (Note 1) (mA)	I _{DRM} (A)
3-lead TO-92	250	2	1	250	2

Note 1: I_D (continuous) is limited by maximum rated T_J .

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

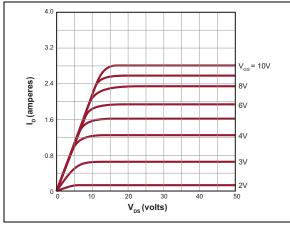


FIGURE 2-1: Output Characteristics.

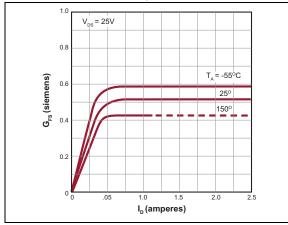


FIGURE 2-2: Transconductance vs. Drain Current.

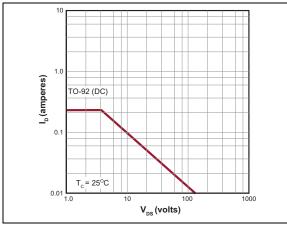


FIGURE 2-3: Maximum Rated Safe Operating Area.

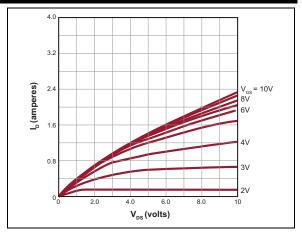


FIGURE 2-4: Saturation Characteristics.

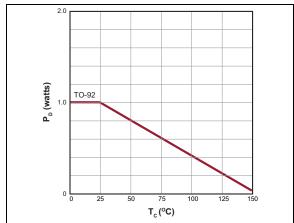


FIGURE 2-5: Power Dissipation vs. Case Temperature.

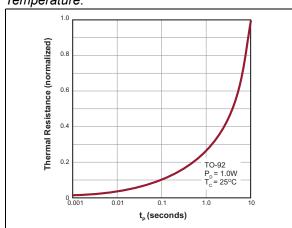


FIGURE 2-6: Thermal Response Characteristics.

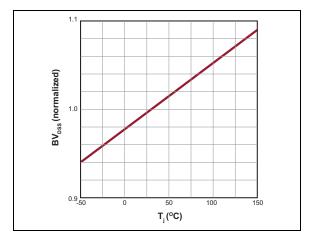
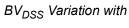


FIGURE 2-7: B
Temperature.



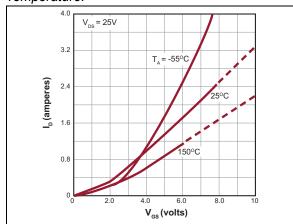


FIGURE 2-8: Transfer Characteristics.

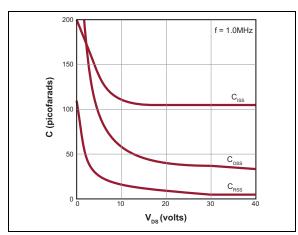


FIGURE 2-9: Capacitance vs. Drain-to-Source Voltage.

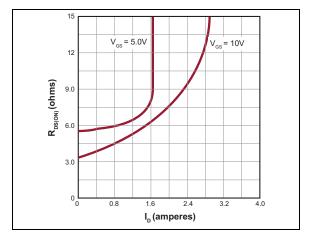


FIGURE 2-10: Current.

On-Resistance vs. Drain

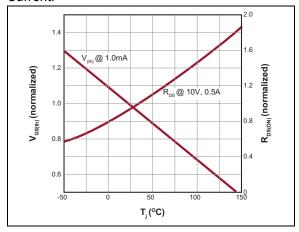


FIGURE 2-11: Temperature.

 $V_{(th)}$ and R_{DS} Variation with

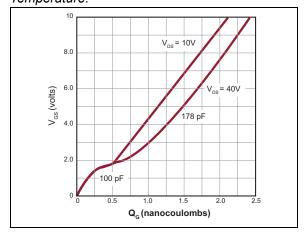


FIGURE 2-12: Characteristics.

Gate Drive Dynamic

TN0620

3.0 PIN DESCRIPTION

Table 3-1 shows the description of pins in TN0620. Refer to **Package Type** for the location of pins.

TABLE 3-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description						
1	Source	Source						
2	Gate	Gate						
3	Drain	Drain						

4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for TN0620.

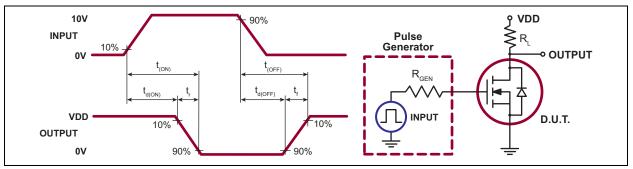


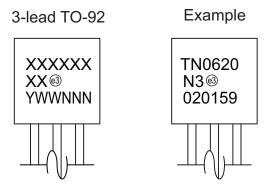
FIGURE 4-1: Switching Waveforms and Test Circuit.

TABLE 4-1: PRODUCT SUMMARY

BV _{DSS} /BV _{DGS} (V)	R _{DS(ON)} (Maximum) (Ω)	I _{D(ON)} (Minimum) (A)	V _{GS(th)} (Maximum) (V)
200	6	1	1.6

5.0 PACKAGING INFORMATION

5.1 Package Marking Information



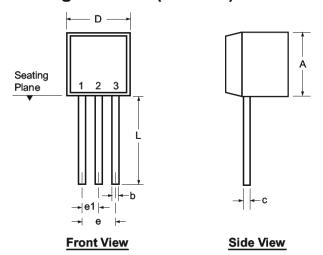
Legend: XX...X Product Code or Customer-specific information
Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')
NNN Alphanumeric traceability code

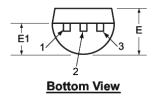
© Pb-free JEDEC® designator for Matte Tin (Sn)

* This package is Pb-free. The Pb-free JEDEC designator (©3)
can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

3-Lead TO-92 Package Outline (L/LL/N3)





Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symb	ool	Α	b	С	D	Е	E1	е	e1	L
MIN	MIN	.170	.014 [†]	.014 [†]	.175	.125	.080	.095	.045	.500
Dimensions (inches)	NOM	-	-	-	-	-	-	-	-	-
(inches)	MAX	.210	.022 [†]	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.
* This dimension is not specified in the JEDEC drawing.
† This dimension differs from the JEDEC drawing.

Drawings not to scale.

TN0620

NOTES:

APPENDIX A: REVISION HISTORY

Revision A (July 2020)

- Converted Supertex Doc# DSFP-TN0620 to Microchip DS20005936A
- · Changed the package marking format
- Updated the packing medium of TN0620 TO-92 N3 P002 media type from 2000/Reel to 2000/Reel (Reverse T/R) to align it with the actual BQM
- Updated the packing medium of TN0620 TO-92 N3 P014 media type from 2000/Reel to 2000/Reel (Ammo Pack) to align it with the actual BQM
- Removed the TN0620 T0-92 N3 P003, P005, and P013 media types
- Made minor text changes throughout the document

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

PART NO	<u>. xx</u>		- X - X	Examples:	
Device	Packa Optio	_	Environmental Media Type	a) TN0620N3-G:	N-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead TO-92,1000/Bag
Device:	TN0620	=	N-Channel Enhancement-Mode Vertical DMOS FET	b) TN0620N3-G-P002:	N-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead TO-92, 2000/Reel
Package:	N3	=	3-lead TO-92		(Reverse T/R)
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package	c) TN0620N3-G-P014:	N-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead TO-92, 2000/Reel
Media Types:	(blank)	=	1000/Bag for an N3 Package		(Ammo Pack)
	P002	=	2000/Reel (Reverse T/R) for an N3 Package		
	P014	=	2000/Reel (Ammo Pack) for an N3 Package		

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